



FEATURES

- Visible light response
- Sintered construction
- Low cost

DESCRIPTION

The **PDV-P8001** are (CdS), Photoconductive photocells designed to sense light from 400 to 700 nm. These light dependent resistors are available in a wide range of resistance values. They're packaged in a two leaded plastic-coated ceramic header.

APPLICATIONS

- Camera exposure
- Shutter controls
- Night light Controls

ABSOLUTE MAXIMUM RATING (TA)= 23°C UNLESS OTHERWISE NOTED

SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{pk}	Applied Voltage		150	V
P _{d Δp0/Δt}	Continuous Power Dissipation		100	mW/°C
T _O	Operating and Storage Temperature	-30	+75	°C
T _S	Soldering Temperature*		+260	°C

* 0.200 inch from base for 3 seconds with heat sink.

ELECTRO-OPTICAL CHARACTERISTICS RATING (TA)= 23°C UNLESS OTHERWISE NOTED

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
R _D	Dark Resistance	After 10 sec. @ 10 Lux @ 2856 °K	0.2			MΩ
R _I	Illuminated Resistance	10 Lux @ 2856 °K	3		11	KΩ
S	Sensitivity	$\frac{\text{LOG}(R_{100})-\text{LOG}(R_{10})^{**}}{\text{LOG}(E_{100})-\text{LOG}(E_{10})^{***}}$		0.6		Ω/Lux
λ _{range}	Spectral Application Range	Flooded	400		700	nm
λ _{peak}	Spectral Application Range	Flooded		520		nm
t _r	Rise Time	10 Lux @ 2856 °K		55		ms
T _f	Fall Time	After 10 Lux @ 2856 °K		20		ms

**R100, R10: cell resistances at 100 Lux and 10 Lux at 2856 °K respectively .

***E100, E10: luminances at 100 Lux and 10 Lux 2856 °K respectively.

Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.